AUTHOR INDEX

ACKER, E., S. HAUSSÜHL und K. RECKER, Züchtung und physikalische Eigenschaften von monoklinem Zinndifluorid **13/14** (1972) 467
ADAMS, A. C. and K. A. JACKSON, Computer simulation of vapor deposition **13/14** (1972) 144
ADAMSKI, J. A., *see* KHAMBATTA **13/14** (1972) 710
ALBINET, G., *see* SUZANNE **13/14** (1972) 164
ALEXANDER, E., *see* STEINBERGER **13/14** (1972) 285
ALLAIS, G., *see* MONFORT **13/14** (1972) 829
AMOUNT, R., *see* TOUDIC **13/14** (1972) 519
AMOUNT, R., *see* PASSARET **13/14** (1972) 524
ANDRÉ, E., J. M. LEDUC and M. MAHIEU, Liquid phase epitaxy of $Ga_{1-x}Al_xAs$ **13/14** (1972) 663
ANTHONY, A. M., *see* VU TIEN **13/14** (1972) 601
ANTHONY, T. R., *see* CLINE **13/14** (1972) 790
ARIZUMI, T., *see* NISHINAGA **13/14** (1972) 346
ARIZUMI, T. and N. KOBAYASHI, Theoretical studies of the temperature distribution in a crystal being grown by the Czochralski method **13/14** (1972) 615
AUBRÉE, J., Tirage du niobate de calcium monocristallin dopé au néodyme **13/14** (1972) 675
AUST, K. T., Principles of crystal growth from the solid state in relation to the preparation of large cyrstals . . . **13/14** (1972) 57
AUTHIER, A., X-ray topography as a tool in crystal growth studies **13/14** (1972) 34
AVIGAL, Y., *see* SCHIEBER **13/14** (1972) 579
AVIGNON, M., Shape stability of two-dimensional nucleus **13/14** (1972) 113

BAN, V. S., *see* DISMUKES **13/14** (1972) 365
BARSUKOVA, M. L., V. A. KUZNETSOV, A. N. LOBACHEV and YU. V. SHALDIN, Hydrothermal crystallisation and some properties of bismuth titanates **13/14** (1972) 530
BAUDELET, B., *see* G'SELL **13/14** (1972) 252
BAYON, J. F., *see* TOUDIC **13/14** (1972) 519
BAYON, J. F., *see* PASSARET **13/14** (1972) 524
BEDNOWITZ, A. L., *see* O'KANE **13/14** (1972) 624
BELIN, C., J. J. BRISSOT and R. E. JESSE, The growth of calcite single crystals by travelling solvent zone melting . . **13/14** (1972) 597
BELL, P. S., *see* BILLINGHAM **13/14** (1972) 693
BELOUET, CHR., Kinetics of vapour-phase epitaxial growth of $GaAs_{1-x}P_x$ **13/14** (1972) 342
BELT, R. F., R. C. PUTTBACH and D. A. LEPORE, Crystal growth and perfection of large Nd:YAG single crystals . **13/14** (1972) 268
BELT, R. F., *see* DHARMARAJAN **13/14** (1972) 535
BENNEMA, P., *see* GILMER **13/14** (1972) 148
BERTOCCI, C., *see* BERTOCCI **13/14** (1972) 427
BERTOCCI, U., C. BERTOCCI and B. C. LARSON, Observations on the electrocrystallization of copper **13/14** (1972) 427
BIENFAIT, M., *see* SUZANNE **13/14** (1972) 164
BILLINGHAM, J., P. S. BELL and M. H. LEWIS, The crystal growth of transition metal interstitial compounds by a floating zone technique **13/14** (1972) 693
BINSBERGEN, F. L., Study of molecular phenomena in the nucleation of crystallisation by computer simulation and application to polymer crystallisation theory **13/14** (1972) 44
BLANIÉ, F. et J. LE HÉRICY, Croissance, par recristallisation secondaire, de gros cristaux exempts de macles dans le cuivre purifié par fusion de zone **13/14** (1972) 834
BLANK, S. L., *see* NIELSEN **13/14** (1972) 702
BLODGETT, J. A., *see* GLICKSMAN **13/14** (1972) 68
BLOEM, J., Doping in chemically vapour deposited epitaxial silicon **13/14** (1972) 302
BOLLING, G. F., *see* CISSÉ **13/14** (1972) 777

BOTSARIS, G. D., *see* DENK, JR. **13/14** (1972) 493

BOTTELIER, P. et F. BOUILLON, Structure de monocristaux d'alliage cuivre-nickel fabriqués par la technique de Bridgman **13/14** (1972) 823

BOUILLON, F., *see* BOTTELIER **13/14** (1972) 823

BOWEN, H. K., W. D. KINGERY, M. KINOSHITA and C. A. GOODWIN, Chemical vapor transport of transition metal oxide solid solutions **13/14** (1972) 402

BRADA, Y., *see* STEINBERGER **13/14** (1972) 285

BRANDER, R. W., *see* CALLAGHAN **13/14** (1972) 397

BRENNER, W., *see* GROCHOWSKI **13/14** (1972) 843

BRISSOT, J. J., *see* BELIN **13/14** (1972) 597

BROCHIER, A., P. COEURE, B. FERRAND, J. C. GAY, J. C. JOUBERT, J. MARESCHAL, J. C. VIGUIE, J. C. MARTIN-BINACHON et J. SPITZ, Hétéroépitaxie de couches minces de grenat de fer–yttrium par méthode de flux et synthèse hydrothermale **13/14** (1972) 571

BUDEVSKI, E., On the mechanism of electrocrystallization **13/14** (1972) 93

BYRNE, J. G., *see* SHIM **13/14** (1972) 410

CALLAGHAN, M. and R. W. BRANDER, A new system for the chemical vapour deposition of SiC **13/14** (1972) 397

CARIDES, J. N., *see* VOORHOEVE **13/14** (1972) 167

CARRUTHERS, J. R. and M. GRASSO, The stabilities of floating liquid zones in simulated zero gravity **13/14** (1972) 611

CASEY, JR., H. C. and M. B. PANISH, The influence of the electrical properties of the solid phase on impurity incorporation during crystal growth **13/14** (1972) 818

CHAKRAVERTY, B. K., *see* NGUYEN **13/14** (1972) 174

CHALLETON, D., *see* DAVAL **13/14** (1972) 706

CHALMERS, B., H. E. LABELLE, JR. and A. I. MLAVSKY, Edge-defined, film-fed crystal growth **13/14** (1972) 84

CHAMPIER, G., *see* G'SELL **13/14** (1972) 252

CHANE, J. P., L. HOLLAN et C. SCHILLER, Etude de l'épitaxie localisée du GaAs **13/14** (1972) 325

CHAPMAN, A. T., R. J. GERDES, J. C. WILSON and G. W. CLARK, Unidirectional solidification behavior in refractory oxide–metal systems **13/14** (1972) 765

CHAUDHURI, A. K., *see* WIEDEMEIER **13/14** (1972) 393

CHEVY, A., *see* KUHN **13/14** (1972) 380

CINTI, R., *see* NGUYEN **13/14** (1972) 174

CIOCCOLANI, A., *see* RICARD **13/14** (1972) 718

CISSÉ, J., G. F. BOLLING and H. W. KERR, Crystallographic orientations between aluminum growth from the melt and various titanium compounds **13/14** (1972) 777

CLARK, G. W., *see* CHAPMAN **13/14** (1972) 765

CLINE, H. E. and T. R. ANTHONY, The migration of liquid droplets in solids **13/14** (1972) 790

COEURE, P., *see* BROCHIER **13/14** (1972) 571

COMBRADE, P. et M. TURPIN, Solidification monovariante d'alliages ternaires; application à la fusion de zone . . **13/14** (1972) 751

CORISH, J. and C. D. O'BRIAIN, The growth and dissolution of silver whiskers **13/14** (1972) 62

COX, D. E. and F. C. MERKERT, The preparation, crystal growth and perfection of double halides of $CsNiCl_3$ type . **13/14** (1972) 282

CROKER, M. N., *see* FIDLER **13/14** (1972) 739

CROWTHER, A. G., Preliminary investigation into the growth of ice crystals from the vapour in an electric field in the temperature range −11 to −15°C **13/14** (1972) 241

DABU, R., *see* NICOLAU **13/14** (1972) 462

DAS, B. N., *see* WOLFF **13/14** (1972) 186

DAVAL, J., D. CHALLETON et J. MARESCHAL, Croissance de monocristaux d'orthoferrite d'yttrium par tirage Czochralski **13/14** (1972) 706

DAWSON, R. D., *see* ELWELL **13/14** (1972) 555

DE JONG, E. J., *see* OTTENS **13/14** (1972) 500

DELOCHE, J., Y. MALMEJAC et B. SCHAUB, Etude des conditions de croissance de monocristaux de beryllium . **13/14** (1972) 814

DEMIANETS, L. N., *see* LOBACHEV **13/14** (1972) 540

DENK, JR., E. G. and G. D. BOTSARIS, Fundamental studies in secondary nucleation from solution **13/14** (1972) 493

DESCHANVRES, A., *see* MONFORT **13/14** (1972) 829

DEVRIES, R. C. and J. F. FLEISCHER, Phase equilibria pertinent to the growth of cubic boron nitride . . . **13/14** (1972) 88

DHARMARAJAN, R., R. F. BELT and R. C. PUTTBACH, Hydrothermal and flux growth of zircon crystals . . . **13/14** (1972) 535

DISMUKES, J. P., W. M. YIM and V. S. BAN, Epitaxial growth and properties of semiconducting ScN. . . . **13/14** (1972) 365

DONIKA, F. G., *see* RADAUTSAN **13/14** (1972) 385

DUNNING, W. J., *see* PILKINGTON **13/14** (1972) 454

DURAND, F., *see* DURAND-CHARRE **13/14** (1972) 747

DURAND-CHARRE, M. and F. DURAND, Effects of growth rate on the morphology of monovariant eutectics: MnSb–(Sb, Bi) and MnSb–(Sb, Sn) **13/14** (1972) 747

DUVAL, X., *see* THOMY **13/14** (1972) 159

ECKERT, J., *see* MROCZKOWSKI **13/14** (1972) 549
ELWELL, D. and R. D. DAWSON, The variation of crystal growth rate with supersaturation in fluxed melts . . . **13/14** (1972) 555
EMELIANOVA, E. N., *see* LOBACHEV **13/14** (1972) 540
EPELBOIN, I., F. LENOIR et R. WIART, Etude par analyse de l'impédance cathodique des processus élémentaires de la croissance cristalline d'un dépôt électrolytique **13/14** (1972) 417

FALCKENBERG, R., Growth of stoichiometric Mg–Al spinel single crystals by a modified Verneuil technique . . **13/14** (1972) 723
FAUST, JR., J. W., *see* LIAW **13/14** (1972) 471
FAUST, JR., J. W., *see* LIAW **13/14** (1972) 772
FEHMER, H. und W. UELHOFF, Die Züchtung versetzungsfreier Kupfereinkristalle **13/14** (1972) 257
FEIGELSON, R. S., G. W. MARTIN and B. C. JOHNSON, Crystal growth and properties of some alkali metal metavanadates **13/14** (1972) 686
FERRAND, B., *see* BROCHIER **13/14** (1972) 571
FIDLER, R. S., M. N. CROKER and R. W. SMITH, The thermodynamics and morphologies of eutectics containing compound phases **13/14** (1972) 739
FIGLARZ, M., *see* LE BIHAN **13/14** (1972) 458
FLEISCHER, J. F., *see* DEVRIES **13/14** (1972) 88
FRANK, F. C., The future of crystal growth **13/14** (1972) 9
FRANK, F. C., An outline of nucleation theory **13/14** (1972) 154
FRANKE, W., *see* HEIMANN **13/14** (1972) 202
FREUND, A. and J. SCHNEIDER, Two new experimental diffraction methods for a precise measurement of crystal perfection **13/14** (1972) 247
FREUND, A., P. GUINET, J. MARESCHAL, F. RUSTICHELLI et F. VANONI, Cristaux à gradient de maille **13/14** (1972) 726
FREY, M., *see* LEDÉSERT **13/14** (1972) 207

GABIS, V., *see* VU TIEN **13/14** (1972) 601
GARABEDIAN, H. and R. F. STRICKLAND-CONSTABLE, Collision breeding of crystal nuclei: sodium chlorate. I. . . **13/14** (1972) 506
GARSIDE, J., C. GASKA and J. W. MULLIN, Crystal growth rate studies with potassium sulphate in a fluidized bed crystallizer **13/14** (1972) 510
GÄRTNER, K. J., K. F. RITTINGHAUS, A. SEEGER and W. UELHOFF, An electronic device including a TV-system for controlling the crystal diameter during Czochralski growth **13/14** (1972) 619
GARTON, G., S. H. SMITH and B. M. WANKLYN, Crystal growth from the flux systems $PbO–V_2O_5$ and $Bi_2O_3–V_2O_5$ **13/14** (1972) 588
GASKA, C., *see* GARSIDE **13/14** (1972) 510
GAY, J. C., *see* BROCHIER **13/14** (1972) 571
GERDES, R. J., *see* CHAPMAN **13/14** (1972) 765
GIELISSE, P. J., *see* KHAMBATTA **13/14** (1972) 710
GILLET, M., *see* GILLET **13/14** (1972) 212
GILLET, E. et M. GILLET, Croissance continue, à partir de germes a symétrie quinaire, des cristallites 'multiples' formés lors de la nucléation hétérogène **13/14** (1972) 212
GILMER, G. H. and P. BENNEMA, Computer simulation of crystal surface structure and growth kinetics . . . **13/14** (1972) 148
GLASNER, A. and M. TASSA, The thermal effects of nucleation and crystallization of KBr solutions. I. Experimental and mathematics, illustrated **13/14** (1972) 441
GLICKSMAN, M. E., R. J. SCHAEFER and J. A. BLODGETT, Holographic study of crystal growth **13/14** (1972) 68
GLICKSMAN, M. E. and C. L. VOLD, Gradient hot-stage electron microscopy of binary metallic solid/liquid interfaces **13/14** (1972) 73
GOLDSZTAUB, S., *see* MUSSARD **13/14** (1972) 445
GOODRUM, J. W., Solution top-seeding: growth of GeO_2 polymorphs **13/14** (1972) 604
GOODWIN, C. A., *see* BOWEN **13/14** (1972) 402
GRABMAIER, B. C. and J. G. GRABMAIER, Dislocation-free GaAs by the liquid encapsulation technique . . . **13/14** (1972) 635
GRABMAIER, J. G., *see* GRABMAIER **13/14** (9172) 635
GRANDIN DE L'EPREVIER, A., *see* VU TIEN **13/14** (1972) 601
GRASSO, M., *see* CARRUTHERS **13/14** (1972) 611
GRILL, A., *see* SCHIEBER **13/14** (1972) 579
GROCHOWSKI, E. and W. BRENNER, The effects of selenide molecular transformations on electrical resistivity . **13/14** (1972) 843
G'SELL, C., B. BAUDELET et G. CHAMPIER, Perfection de cristaux d'aluminium en fonction des traitements thermiques subis **13/14** (1972) 252
GUINET, P., *see* FREUND **13/14** (1972) 726
GULITZ, L., *see* O'KANE **13/14** (1972) 624

HAUSSÜHL, S., *see* ACKER **13/14** (1972) 467

HEIMANN, R., W. FRANKE and R. LACMANN, Dissolution forms of single crystal spheres of rutile 13/14 (1972) 202
HOFFMANN, F., *see* PASCARD 13/14 (1972) 225
HOLLAN, L., et C. SCHILLER, Etude de l'anisotropie de la croissance épitaxiale de GaAs en phase vapeur . . 13/14 (1972) 319
HOLLAN, L., *see* CHANE 13/14 (1972) 325
HOLLIDAY, C. H., *see* MULLIN 13/14 (1972) 629
HUBERT, J.-C., W. KURZ et B. LUX, Croissance en solidification dirigée de l'eutectique quasi-binaire Ni_3Al–Ni_3Ta 13/14 (1972) 757
HUIGE, N. J. J. and H. A. C. THIJSSEN, Production of large crystals by continuous ripening in a stirrer tank . 13/14 (1972) 483
HURLE, D. T. J., Hydrodynamics, convection and crystal growth 13/14 (1972) 39

IIDA, S. and K. ITO, Morphological studies on selective growth of GaAs 13/14 (1972) 336
ILEGEMS, M., Vapor epitaxy of gallium nitride 13/14 (1972) 360
INO, S., *see* OGAWA 13/14 (1972) 48
IRENE, E. A., *see* WIEDEMEIER 13/14 (1972) 393
ITO, K., *see* IIDA 13/14 (1972) 336
ITTU, M., *see* NICOLAU 13/14 (1972) 462

JACKSON, K. A., *see* LEAMY 13/14 (1972) 140
JACKSON, K. A., *see* ADAMS 13/14 (1972) 144
JANSE, A. H., *see* OTTENS 13/14 (1972) 500
JESSE, R. E., *see* BELIN 13/14 (1972) 597
JOHNSON, B. C., *see* FEIGELSON 13/14 (1972) 686
JONES, P. L., *see* LILLEY 13/14 (1972) 371
JOUBERT, J. C., *see* BROCHIER 13/14 (1972) 571

KALMAN, Z. H., *see* STEINBERGER 13/14 (1972) 285
KASHCHIEV, D., Nucleation in external electric field 13/14 (1972) 128
KASHCHIEV, D., *see* MARKOV 13/14 (1972) 131
KENNEDY, J. K. and W. D. POTTER, Epitaxial deposition of degenerate n-type layers of Ge on GaAs 13/14 (1972) 315
KERR, H. W., *see* CISSÉ 13/14 (1972) 777
KHAMBATTA, F. B., P. J. GIELISSE, M. P. WILSON, JR., J. A. ADAMSKI and CH. SAHAGIAN, Initial thermal model of the flame fusion crystal growth process 13/14 (1972) 710
KIFLAWI, I., *see* STEINBERGER 13/14 (1972) 285
KIMURA, M., *see* TAKAHASHI 13/14 (1972) 681
KINGERY, W. D., *see* BOWEN 13/14 (1972) 402
KINOSHITA, M., *see* BOWEN 13/14 (1972) 402
KITTERMAN, J. H. and D. R. WINDER, Growth of cadmium whiskers in various atmospheres 13/14 (1972) 198
KOBAYASHI, N., *see* ARIZUMI 13/14 (1972) 615
KRISHNAN, R., Some features of the growth of single crystals of the $Y_3Fe_{5-x}Cr_xO_{12}$ system 13/14 (1972) 582
KUHN, A., A. CHEVY and E. LENDVAY, Growth of GaSe single crystals from the vapor phase 13/14 (1972) 380
KURZ, W., *see* HUBERT 13/14 (1972) 757
KUZMINA, I. P., *see* LOBACHEV 13/14 (1972) 540
KUZNETSOV, V. A., *see* BARSUKOVA 13/14 (1972) 530
KWAP, T. W., *see* O'KANE 13/14 (1972) 624

LABELLE, JR., H. E., *see* CHALMERS 13/14 (1972) 84
LACMANN, R., *see* HEIMANN 13/14 (1972) 202
LACMANN, R. and I. N. STRANSKI, The growth of snow crystals 13/14 (1972) 236
LARSON, B. C., *see* BERTOCCI 13/14 (1972) 427
LAUDISE, R. A., Single crystals for bubble domain memories 13/14 (1972) 27
LEAMY, H. J. and K. A. JACKSON, Surface structure and surface diffusion: the fcc (110)interface 13/14 (1972) 140
LE BIHAN, S. et M. FIGLARZ, Croissance de l'hydroxyde de nickel $Ni(OH)_2$ à partir d'un hydroxyde de nickel turbostratique 13/14 (1972) 458
LECKEBUSCH, R. und K. RECKER, Perfektion von CaF_2-Einkristallen in Abhängigkeit von der Zuchttechnik . . 13/14 (1972) 276
LEDÉSERT, M. et M. FREY, Croissance des cristaux de cyanure mercurique orientés par rapport à la matrice de cristaux de leur solvate avec le tétrahydrofuranne 13/14 (1972) 207
LEDUC, J. M., *see* ANDRÉ 13/14 (1972) 663
LEFAUCHEUX, F., Observations de dislocations dans des calcites synthétiques 13/14 (1972) 272
LEGEROS, J. P., *see* LEGEROS 13/14 (1972) 476
LEGEROS, R. Z. and J. P. LEGEROS, Brushite crystals grown by diffusion in silica gel and in solution 13/14 (1972) 476
LE HÉRICY, J., *see* BLANIÉ 13/14 (1972) 834
LENDVAY, E., *see* KUHN 13/14 (1972) 380
LENOIR, F., *see* EPELBOIN 13/14 (1972) 417

LEPORE, D. A., *see* BELT **13/14** (1972) 268
LESOULT, G., Thermodynamique de la solidification eutectique **13/14** (1972) 733
LEWIS, M. H., *see* BILLINGHAM **13/14** (1972) 693
LIAW, H. M. and J. W. FAUST, JR., Growth kinetics of lead dendrites in gels **13/14** (1972) 471
LIAW, H. M. and J. W. FAUST, JR., Effect of modes crystallization on habit and morphology of copper dendrites . **13/14** (1972) 772
LILLEY, P., P. L. JONES and C. N. W. LITTING, The epitaxial growth of zinc sulphide on silicon by forced vapour transport in argon flow **13/14** (1972) 371
LITTING, C. N. W., *see* LILLEY **13/14** (1972) 371
LOBACHEV, A. N., *see* BARSUKOVA **13/14** (1972) 530
LOBACHEV, A. N., L. N. DEMIANETS, I. P. KUZMINA and E. N. EMELIANOVA, Investigation of the solubility and crystallization kinetics of sodium–zinc germanate (Na_2ZnGeO_4) under hydrothermal conditions **13/14** (1972) 540
LORIERS, J., *see* MAKRAM. **13/14** (1972) 585
LORIERS, J. et M. VICHR, Synthèse de monocristaux de vanadate d'yttrium par la méthode de tirage en flux. . . **13/14** (1972) 593
LUX, B., *see* HUBERT **13/14** (1972) 757

MACEWAN, W. R., *see* MULLIN **13/14** (1972) 629
MAHIEU, M., *see* ANDRÉ **13/14** (1972) 663
MAISSEU, A., *see* MONFORT **13/14** (1972) 829
MAKRAM, H., L. TOURON and J. LORIERS, Phase relations in the system Fe_2O_3–B_2O_3 and its application in single crystal growth of $FeBO_3$ **13/14** (1972) 585
MALMEJAC, Y., *see* DELOCHE. **13/14** (1972) 814
MANASEVIT, H. M., The use of metalorganics in the preparation of semiconductor materials: growth on insulating substrates **13/14** (1972) 306
MARDIX, S., *see* STEINBERGER **13/14** (1972) 285
MARESCHAL, J., *see* BROCHIER **13/14** (1972) 571
MARESCHAL, J., *see* DAVAL **13/14** (1972) 706
MARESCHAL, J., *see* FREUND **13/14** (1972) 726
MARKOV, I. and D. KASHCHIEV, The role of active centers in the kinetics of new phase formation **13/14** (1972) 131
MARTIN, G. W., *see* FEIGELSON **13/14** (1972) 686
MARTIN-BINACHON, J. C., *see* BROCHIER **13/14** (1972) 571
MATEIKA, D., Growth of MnTe single crystals from nonstoichiometric melts by liquid encapsulation **13/14** (1972) 698
MCFARLANE III, S. H., *see* WANG **13/14** (1972) 262
MENAUCOURT, J., *see* THOMY **13/14** (1972) 159
MERENDA, P., Une nouvelle méthode d'épitaxie en phase vapeur d'arseniure de gallium de haute pureté . . . **13/14** (1972) 331
MERKERT, F. C., *see* COX **13/14** (1972) 282
MILCHEV, A., *see* TOSCHEV **13/14** (1972) 123
MLAVSKY. A. I., *see* CHALMERS **13/14** (1972) 84
MONFORT, Y., A. MAISSEU, G. ALLAIS et A. DESCHANVRES, Croissance orientée des sous oxydes de niobium dans la matrice de niobium **13/14** (1972) 829
MOTTRAM, A., *see* PEAKER **13/14** (1972) 651
MOUSTIA, I. G., *see* RADAUTSAN **13/14** (1972) 385
MROCZKOWSKI, S. and J. ECKERT, Hydrothermal growth of single crystals of heavy rare earth hydroxides . . **13/14** (1972) 549
MULLIN, J. B., W. R. MACEWAN, C. H. HOLLIDAY and A. E. V. WEBB, Pressure balancing: a technique for suppressing dissociation during the melt-growth of compounds **13/14** (1972) 629
MULLIN, J. B., A. ROYLE, B. W. STRAUGHAN, P. J. TUFTON and E. W. WILLIAMS, Crystal growth and properties of group IV doped indium phosphide **13/14** (1972) 640
MULLIN, J. W., *see* NIENOW **13/14** (1972) 488
MULLIN, J. W., *see* GARSIDE. **13/14** (1972) 510
MUSSARD, F. et S. GOLDSZTAUB, Sur la croissance du chlorate de sodium en solution **13/14** (1972) 445
MUTAFTSCHIEV, B., *see* ZELL. **13/14** (1972) 231

NANAMATSU, S., *see* TAKAHASHI **13/14** (1972) 681
NASSAU, K., Dr. A. V. L. Verneuil: The man and the method **13/14** (1972) 12
NASSAU, K. and J. W. SHIEVER, Vapor growth of II–VI compounds and the identification of donors and acceptors **13/14** (1972) 375
NEATE, B. W., *see* ROBERTSON **13/14** (1972) 576
NENOW, D., On the variational formulation of the problem of surface equilibrium of crystals **13/14** (1972) 183
NGUYEN DUC CHINH, Méthode de dopage au chrome dans la préparation du rubis hydrothermal **13/14** (1972) 545
NGUYEN, T. T. A., R. CINTI and B. K. CHAKRAVERTY, Condensation of indium films on silicon substrates observed by mass spectrometric technique **13/14** (1972) 174
NICOLAU, I. F., M. ITTU et R. DABU, Méthode de croissance en solution des monocristaux par l'addition graduelle d'un réactif **13/14** (1972) 462
NIELSEN, J. W., *see* VON NEIDA **13/14** (1972) 647

NIELSEN, J. W. and S. L. BLANK, Crystal growth and phase equilibrium studies in the system (R. E.)$_2O_3$–Fe_2O_3 **13/14** (1972) 702
NIENOW, A. W., P. D. B. RUJAC and J. W. MULLIN, Slip velocities in agitated vessel crystallisers **13/14** (1972) 488
NISHINAGA, T., H. OGAWA, H. WATANABE and T. ARIZUMI, Vapor growth of boron monophosphide using open and closed tube processes **13/14** (1972) 346
NISHIZAWA, J.-I., T. TERASAKI and M. SHIMBO, Layer growth in silicon epitaxy **13/14** (1972) 297

O'BRIAIN, C. D., *see* CORISH **13/14** (1972) 62
OGAWA, H., *see* NISHINAGA **13/14** (1972) 346
OGAWA, S. and S. INO, Formation of multiply-twinned particles on alkali halide crystals by vacuum evaporation and their structures **13/14** (1972) 48
OGAWA, T. and M. UCHIDA, Growth and textures of ZnS crystals **13/14** (1972) 292
OHACHI, T. and I. TANIGUCHI, Controlled filamentary growth of silver from silver compounds **13/14** (1972) 191
OHTSUKI, O., *see* UEDA **13/14** (1972) 668
O'KANE, D. F., T. W. KWAP, L. GULITZ and A. L. BEDNOWITZ, Infrared TV system of computer controlled Czochralski crystal growth **13/14** (1972) 624
OSTER, L. J., *see* VON NEIDA **13/14** (1972) 647
OTTENS, E. P. K., A. H. JANSE and E. J. DE JONG, Secondary nucleation in a stirred vessel cooling crystallizer . **13/14** (1972) 500
OUVRARD, J., R. WANDJI et B. ROQUES, Contribution des réactions chimiques de transport à l'étude structurale des siliciures de fer **13/14** (1972) 406

PANISH, M. B., *see* CASEY, JR. **13/14** (1972) 818
PAPARODITIS, C. and R. SURYANARAYANAN, Preparation of rare earth chalcogenide thin films by the co-evaporation technique **13/14** (1972) 389
PASCARD, H., C. QUINTANA, F. HOFFMANN et C. SELLA, Recristallisation de couches minces d'argent sur le mica **13/14** (1972) 225
PASSARET, M., *see* TOUDIC **13/14** (1972) 519
PASSARET, M., Y. TOUDIC, A. REGRENY, R. AMOUNT et J. F. BAYON, Recristallisation de TiO_2, GeO_2, SiO_2, $Si_{1-x}Ge_xO_2$ en solutions hydrothermales fluorées **13/14** (1972) 524
PEAKER, A. R., P. D. SUDLOW and A. MOTTRAM, Solution growth of gallium phosphide p-n junctions by liquid phase epitaxy **13/14** (1972) 651
PILKINGTON, G. and W. J. DUNNING, The growth of potassium chloride crystals in the presence of lead . . . **13/14** (1972) 454
PLOOG, K., P. RAUH, W. STOEGER und H. SCHMIDT, Binäre Verbindungen des Bors mit Elementen der V. Hauptgruppe unter Erhaltung von ikosaedrischen Grundgerüsten: tetragonales Bornitrid und rhomboedrisches Borphosphid **13/14** (1972) 350
POTARD. C., Calcul des conditions de croissance de cristaux en solution **13/14** (1972) 804
POTTER, W. D., *see* KENNEDY **13/14** (1972) 315
PUTTBACH, R. C., *see* BELT **13/14** (1972) 268
PUTTBACH, R. C., *see* DHARMARAJAN **13/14** (1972) 535

QUINTANA, C., *see* PASCARD **13/14** (1972) 225

RADAUTSAN, S. I., F. G. DONIKA et I. G. MOUSTIA, Croissance de certains polytypes des phases ternaires semiconductrices du système zinc-indium-soufre à partir de la phase gazeuse **13/14** (1972) 385
RAUH, P., *see* PLOOG **13/14** (1972) 350
RECKER, K., *see* LECKEBUSCH **13/14** (1972) 276
RECKER, K., *see* ACKER **13/14** (1972) 467
REED, T. B., *see* STEININGER **13/14** (1972) 106
REGNIER, J., *see* THOMY **13/14** (1972) 159
REGRENY, A., *see* TOUDIC **13/14** (1972) 519
REGRENY, A., *see* PASSARET **13/14** (1972) 524
RICARD, J. et A. CIOCCOLANI, Croissance industrielle et caracterisation de grands monocristaux de saphir par la méthode de Verneuil **13/14** (1972) 718
RITTINGHAUS, K. F., *see* GÄRTNER **13/14** (1972) 619
ROBERTSON, J. M. and B. W. NEATE, Some observations on the growth of YIG under oxygen pressure by the 'fluxed melt' technique **13/14** (1972) 576
ROOS, J. R. and J. S. VERMAAK, On the growth process of Au and Ag on various air- and vacuum-cleaved alkali halide crystals **13/14** (1972) 217
ROQUES, B., *see* OUVRARD **13/14** (1972) 406
ROY, R. and W. B. WHITE, Growth of titanium oxide crystals of controlled stoichiometry and order **13/14** (1972) 78
ROYLE, A., *see* MULLIN **13/14** (1972) 640
RUJAC, P. D. B., *see* NIENOW **13/14** (1972) 488
RUSTICHELLI, F., *see* FREUND **13/14** (1972) 726

SAHAGIAN, CH., *see* KHAMBATTA **13/14** (1972) 710
SCHAEFER, R. J., *see* GLICKSMAN **13/14** (1972) 68
SCHAUB, B., *see* DELOCHE **13/14** (1972) 814
SCHEEL, H. J., Accelerated crucible rotation: a novel stirring technique in high-temperature solution growth . . **13/14** (1972) 560
SCHIEBER, M., A. GRILL and Y. AVIGAL, Flux growth and magnetic characterization of calcium-silicon substituted ytterbium and yttrium iron garnets **13/14** (1972) 579
SCHILLER, C., *see* HOLLAN **13/14** (1972) 319
SCHILLER, C., *see* CHANE **13/14** (1972) 325
SCHMIDT, H., *see* PLOOG **13/14** (1972) 350
SCHNEIDER, J., *see* FREUND **13/14** (1972) 247
SCHULTZE, W. A., On the morphology of electrocrystallized copper **13/14** (1972) 421
SEEGER, A., *see* GÄRTNER **13/14** (1962) 619
SELLA, C., *see* PASCARD **13/14** (1972) 225
SHALDIN, YU. V., *see* BARSUKOVA **13/14** (1972) 530
SHANKS, H. R., Growth of tungsten bronze crystals by fused salt electrolysis. **13/14** (1972) 433
SHIEVER, J. W., *see* NASSAU **13/14** (1972) 375
SHIM, H. S. and J. G. BYRNE, The effect of substrate temperature and reactant gas pressure on the chemical vapor deposition of tungsten films **13/14** (1972) 410
SHIMBO, M., *see* NISHIZAWA **13/14** (1972) 297
SHINOHARA, K., *see* UEDA **13/14** (1972) 668
SIGSBEE, R. A., Adatom capture and nuclei growth **13/14** (1972) 135
SMITH, R. W., *see* FIDLER **13/14** (1972) 739
SMITH, R. W., *see* WARR **13/14** (1972) 810
SMITH, S. H., *see* GARTON **13/14** (1972) 588
SPITZ, J., *see* BROCHIER **13/14** (1972) 571
STEINBERGER, I. T., E. ALEXANDER, Y. BRADA, Z. H. KALMAN, I. KIFLAWI and S. MARDIX, Growth and perfection of ZnS crystals grown from the vapor phase **13/14** (1972) 285
STEININGER, J. and T. B. REED, Application of heat pipe technology to crystal growth **13/14** (1972) 106
STEININGER, J. and A. J. STRAUSS, Phase diagrams and crystal growth of pseudobinary alloy semiconductors . **13/14** (1972) 657
STOEGER, W., *see* PLOOG **13/14** (1972) 350
STOYANOV, S., *see* TOSCHEV **13/14** (1972) 123
STRANSKI, I. N., Eine Plauderei über Gleichgewichtsformen von Kristallen **13/14** (1972) 3
STRANSKI, I. N., *see* LACMANN **13/14** (1972) 236
STRAUGHAN, B. W., *see* MULLIN **13/14** (1972) 640
STRAUSS, A. J., *see* STEININGER **13/14** (1972) 657
STRICKLAND-CONSTABLE, R. F., *see* GARABEDIAN **13/14** (1972) 506
SUDLOW, P. D., *see* PEAKER **13/14** (1972) 651
SUREK, T., Molecular phenomena during crystal evaporation **13/14** (1972) 19
SURYANARAYANAN, R., *see* PAPARODITIS **13/14** (1972) 389
SUZANNE, J., G. ALBINET et M. BIENFAIT, Etude par diffraction d'électrons lents de l'adsorption du xénon sur un monocristal du graphite **13/14** (1972) 164

TAKAHASHI, M., S. NANAMATSU and M. KIMURA, The growth of ferroelectric single crystal $Sr_2Nb_2O_7$ by means of the floating zone technique **13/14** (1972) 681
TANIGUCHI, I., *see* OHACHI **13/14** (1972) 191
TASSA, M., *see* GLASNER **13/14** (1972) 441
TERASAKI, T., *see* NISHIZAWA **13/14** (1972) 297
THIJSSEN, H. A. C., *see* HUIGE **13/14** (1972) 483
THOMY, A., J. REGNIER, J. MENAUCOURT et X. DUVAL, Les différentes étapes de la formation d'un film adsorbé de gaz rare ou de méthane sur une surface uniforme de graphite **13/14** (1972) 159
TOLKSDORF, W. and F. WELZ, The effect of local cooling and accelerated crucible rotation on the quality of garnet crystals **13/14** (1972) 566
TOSCHEV, S., A. MILCHEV and S. STOYANOV, On some probabilistic aspects of the nucleation process. . . . **13/14** (1972) 123
TOUDIC, Y., A. REGRENY, M. PASSARET, R. AMOUNT et J. F. BAYON, Nouveau type d'appareillage appliqué à la croissance hydrothermale de monocristaux de cinabre de grandes dimensions **13/14** (1972) 519
TOUDIC, Y., *see* PASSARET **13/14** (1972) 524
TOURON, L., *see* MAKRAM **13/14** (1972) 585
TROOST, S., Crystal growth of sodium triphosphate hexahydrate from aqueous solutions **13/14** (1972) 449
TUFTON, P. J., *see* MULLIN **13/14** (1972) 640
TURPIN, M., *see* COMBRADE **13/14** (1972) 751
TURPIN, M. L., Les matériaux composites à fibres **13/14** (1972) 97
TZAVARAS, A. A. and J. F. WALLACE, Cast steel structures grown under fluid flow **13/14** (1972) 782

UCHIDA, M., *see* OGAWA 13/14 (1972) 292
UEDA, R., O. OHTSUKI, K. SHINOHARA and Y. UEDA, Crystal growth of $Hg_{1-x}Cd_xTe$ using Te as a solvent . . . 13/14 (1972) 668
UEDA, Y., *see* UEDA 13/14 (1972) 668
UELHOFF, W., *see* FEHMER 13/14 (1972) 257
UELHOFF, W., *see* GÄRTNER 13/14 (1972) 619

VANONI, F., *see* FREUND 13/14 (1972) 726
VERMAAK, J. S., *see* ROOS 13/14 (1972) 217
VICHR, M., *see* LORIERS 13/14 (1972) 593
VIGUIE, J. C., *see* BROCHIER 13/14 (1972) 571
VOLD, C. L., *see* GLICKSMAN 13/14 (1972) 73
VON NEIDA, A. R., L. J. OSTER and J. W. NIELSEN, Liquid encapsulated growth of GaP from non-stoichiometric melts 13/14 (1972) 647
VOORHOEVE, R. J. H., R. S. WAGNER and J. N. CARIDES, Study of adsorption and nucleation of cadmium on germanium single crystals by a molecular beam technique 13/14 (1972) 167
VU TIEN, L., A. GRANDIN DE L'EPREVIER, V. GABIS et A. M. ANTHONY, Amélioration de la méthode des flux, synthèse et purification d'un minéral naturel: la forstérite 13/14 (1972) 601

WAGNER, R. S., *see* VOORHOEVE 13/14 (1972) 167
WALLACE, J. F., *see* TZAVARAS 13/14 (1972) 782
WANDJI, R., *see* OUVRARD 13/14 (1972) 406
WANG, C. C. and S. H. MCFARLANE III, Epitaxial growth and characterization of GaP on insulating substrates . 13/14 (1972) 262
WANKLYN, B. M., *see* GARTON 13/14 (1972) 588
WARR, B. D. and R. W. SMITH, The orientation-dependence of the partition coefficient in zinc-base alloy single crystals 13/14 (1972) 810
WATANABE, H., *see* NISHINAGA 13/14 (1972) 346
WEBB, A. E. V., *see* MULLIN 13/14 (1972) 629
WEINSTEIN, M., *see* WOLFF 13/14 (1972) 186
WELZ, F., *see* TOLKSDORF 13/14 (1972) 566
WHITE, W. B., *see* ROY 13/14 (1972) 78
WIART, R., *see* EPELBOIN 13/14 (1972) 417
WIEDEMEIER, H., E. A. IRENE and A. K. CHAUDHURI, Crystal growth by vapor transport of GeSe, $GeSe_2$, and GeTe and transport mechanism and morphology of GeTe 13/14 (1972) 393
WILCOX, W. R., Movement of liquid inclusions by centrifugation 13/14 (1972) 787
WILLIAMS, E. W., *see* MULLIN 13/14 (1972) 640
WILSON, J. C., *see* CHAPMAN 13/14 (1972) 765
WILSON, Jr., M. P., *see* KHAMBATTA 13/14 (1972) 710
WINDER, D. R., *see* KITTERMAN 13/14 (1972) 198
WOLFF, G. A., M. WEINSTEIN and B. N. DAS, A unified approach to habit and crystal growth analysis . . . 13/14 (1972) 186

YIM, W. M., *see* DISMUKES 13/14 (1972) 365
YUE, A. S. and J. T. YUE, The effect of concentration and temperature gradients on solute redistribution . . 13/14 (1972) 797
YUE, J. T., *see* YUE 13/14 (1972) 797

ZELL, J. and B. MUTAFTSCHIEV, Simulation of a crystal–melt interface in a monoatomic system 13/14 (1972) 231

SUBJECT INDEX

Each page number refers to the first page of a given reference

Absorption, optical 389
Adherence 389
Adsorption 3, 159, 164, 167, 174, 302, 417, 519, 524
Agitated vessel 488
Amorphous chalcogenide semiconductors 843
Anomalous solute partition 810

Banding 34, 39, 611
— *see also* Perfection of crystals
Bénard convection cells 39
Bond chain 186
Bond energy ratio 186
Bravais lattice 186
Bridgman method, *see* Melt growth

Cellular growth 68, 84, 647, 747, 782
Centrifugation 787
Charge carrier 651, 668
Charge transfer 417, 668
Chemical transport 27, 331, 336, 346, 380, 393, 402, 406, 668
Chemical vapour deposition 306
Cleavage 186
Clustering 128, 131, 212, 257, 693
Collision breeding 506
Colour centres 276
Composites 751, 757, 765
Computer control 624
Computer simulation 44, 144, 148
— of solute distribution 797
Constitutional supercooling 9, 39, 560, 597, 647, 657
— *see also* Morphological stability
Continuous growth 84
Controlled filamentary growth of silver 191
Controlled profile crystals 84
Convection 39, 417, 560
Cooling finger 566
Creep properties 757
Czochralski method, *see* Melt growth

Defects 34, 93, 131, 247, 257, 276, 285, 380, 427, 458, 519, 647, 693, 702, 814
— *see also* Perfection of crystals
Dendritic growth 68, 84, 191, 236, 471, 593, 747, 772, 782
Diameter control 619
Diffusion 131, 135, 140, 302, 417, 483, 488, 560, 597, 751, 790, 804
Diffusional freezing 657
Dislocations 34, 62, 167, 252, 257, 272, 276, 285, 380, 566, 597 635, 647
— *see also* Perfection of crystals
— non-basal 380
Dislocation bunches 380
Dislocation growth 445
Dissociable compounds 629
Dissolution forms 202
Distribution coefficient 39, 302, 640, 657, 810, 814, 818
Doping 167, 302, 306, 319, 325, 365, 375, 524, 545, 601, 675, 818
— gradients 651

Edge emission 375
Electric field 62, 128, 241, 285, 787
Electrochemical cells 62
Electrocrystallization, *see* Solution growth
Electroluminescence 651
Electrolysis 417, 433
Electrolytic nucleation 123
Electro-optic crystals 624
Encapsulation 635, 698
Epitaxy 27, 48, 167, 202, 217, 225, 262, 297, 302, 306, 315, 319, 325, 331, 336, 342, 346, 360, 371, 397, 571, 651, 777, 814, 818
— *see also* Thin films
Equilibrium form 3, 183, 186, 693
Equimolecular dividing surface 183
Etching 276, 380, 635
Eutectic growth 97, 597, 733, 739, 747, 751, 757, 765
Evaporation 19, 135, 167, 217, 225, 389, 576

Facets 39, 186, 202, 297, 319, 325, 336, 410, 421, 471, 576, 635, 772, 810
Fast growth 84
Fibre composite materials 97
Flatness of surface 225
Floating zone method, *see* Melt growth
Fluidized bed 488, 510
Flux growth, *see* Solution growth
Fluxed melt 555
Fracture 97
Furnace profile 106

Gel growth, *see* Solution growth
Gibbs–Thomson equation 183
Grain boundary 73, 698
Growth orientation 191, 207, 225, 297, 306, 319, 325, 635, 675, 693, 747, 814, 829, 834

Growth spirals 380, 454, 566
Growth by two-dimensional nucleation 445

Habit modification 476
Hard sphere model 213, 217
Heat flow 441, 483, 611, 615, 635, 710, 273
Herring formula 183
Heteroepitaxy 365
High temperature furnace 12, 106, 397, 582, 681, 693, 723, 782
Holography 68
Hydrodynamics 39
Hydrothermal growth, *see* Solution growth

Impact nucleation 506
Impurity distribution 34, 39, 198, 257, 276, 325, 336, 375, 441, 454, 458, 476, 519, 566, 601, 640, 651, 772, 810, 814, 818
Impurity incorporation in semiconductors 818
Inclusions 34, 257, 545, 576, 787
Induction period 510
Induction time 123
Infrared spectroscopy 458
Insulating substrates 306
Interface, crystal–melt, *see* Solid–liquid interface
Interface morphology 739
Interfacial energy, *see* Surface tension
Interlamellar spacing 733
Intermolecular forces 3, 159, 186, 212
Internal friction 681

Kinetic theory 144
Kinetics 140, 202, 342, 417, 458, 540, 790
– of growth 27, 44, 84, 135, 148, 167, 191, 198, 241, 276, 297, 302, 319, 325, 331, 342, 371, 441, 445, 449, 467, 471, 483, 488, 500, 510, 519, 524, 540, 545, 555, 560, 576, 597, 635, 710, 723, 733, 772, 782, 787, 804
– of nucleation 3, 44, 93, 123, 128, 131, 135, 140, 144, 148, 154, 159, 164, 167, 174, 191, 212, 306, 471, 483, 493, 500, 506, 510, 560, 566, 772, 777
Kyropoulos method, *see* Melt growth

Lang method 34, 252, 257, 268, 285, 445
Laser materials 268, 593, 675
Lateral growth 297, 593
Lattice parameter 726
Light emitting diodes 651
Liquid encapsulation 629, 635, 640, 698
Liquid phase epitaxy 804
Local cooling 560, 566
Long range order 693
Luminescent materials 540

Macrostructure 97, 410, 834
Magneli phases 78
Magnetic circular dichroism 389
Magnetic garnets 27
Mass spectrometer 174
Mass transport rate 393
Mechanical deformation 97, 410
Melt growth 647, 710, 718, 273
– by Bridgman method 276, 668, 702
– by Czochralski method 39, 84, 257, 268, 276, 593, 615, 619, 624, 629, 635, 640, 675, 686, 706, 726, 814
— by edge-defined, film-fed growth process 84
— by floating zone method 597, 611, 681, 693, 757
— by Kyropoulos method 276, 604
— by Stockbarger method 276, 698
— by unidirectional solidification 97, 198, 257, 657, 733, 747, 751, 757, 765, 782, 814, 823
— by Verneuil method 12, 710, 723
— — history of 12
— by zone melting 597, 657, 693, 751, 757
Microstructure 73, 402, 406, 410, 421, 471, 693, 739, 747, 772, 782, 829
— flow modified 782
Mobility 342
Model simulation 231
Moiré patterns 34
Monochromator 726
Monovariant solidification 751
Morphological stability 9, 113, 757, 843
Morphology of growth 3, 186, 191, 198, 236, 241, 319, 325, 371, 393, 421, 449, 454, 467, 471, 476, 530, 549, 601, 772

Non-stoichiometric 647
Non-stoichiometric melts 698
Nucleation, *see* Kinetics of –
Nucleation, non-steady state, 123

One-dimensional magnetism 282

PBC-vector 186
Pentagonal structure 212
Perfection
— of crystals 12, 34, 247, 252, 257, 262, 268, 276, 282, 285, 292, 342, 365, 389, 402, 421, 427, 458, 467, 519, 545, 576, 597, 635, 640, 647, 686, 693, 814
Phase changes 159
Phase diagram 406, 530, 545, 549, 585, 657, 693, 698, 702, 751, 757, 818
Phase equilibrium 164
Phase transformation, *see* Solid state growth
Photoluminescence efficiency 647
Photoluminescence spectra 640
p-n junctions 651
Point defects 131, 276, 693
Polymer 44
Polytypism 186, 285, 292, 385, 397
Precipitation 191, 402, 604, 829
Pressure balancing 629
Pulling-flux method, combined, *see* Melt growth by Czochralski method, Solution growth by flux growth
Pyrolysis 350

Recrystallization, *see* Solid state growth
Ripening 483

Secondary nucleation 493, 500, 506
Segregation 39, 611, 640, 751, 797, 810, 823
Selective growth 336
Semiconductors 365, 385, 530, 640, 804
— II–VI 285, 306, 336, 371, 375, 629, 698, 804
— III–V 262, 306, 319, 325, 331, 336, 342, 346, 360, 629, 635, 640, 647, 651, 804, 818
— III–VI 380

— IV–IV 397
— amorphous chalcogenide 843
— magnetic 389
Semiconductor–metal transition, pressure induced 389
Short range order, 693
Slip velocity 488
Small phases 212
Solid–liquid interface 231, 236, 241
Solid state growth 829, 834
— by phase transformation 44, 88, 128, 131, 389, 549, 693, 698, 814, 843
— by recrystallization 225
Solute distribution 611, 657, 747, 751, 797, 810, 814, 823
Solution growth 441, 445, 449, 454, 458, 462, 467, 739, 772
— by electrocrystallization 93, 417, 421, 427, 433
— by flux growth 27, 535, 555, 560, 566, 571, 576, 579, 582, 585, 588, 593, 597, 601, 604
— by gel growth 276, 471, 476
— by hydrothermal growth 27, 519, 524, 530, 535, 540, 545, 549, 571
— industrial 483, 488, 493, 500, 506, 510
— by temperature gradient method 27, 84, 106, 191, 519, 524, 530, 540, 549, 566, 593, 657, 790, 804
Solution seeding 604
Solution turbulence 488
Solution zoning 657
Stability 611, 733
Stacking faults 292
Stimulated Raman scattering 686
Stockbarger method, *see* Melt growth
Stoichiometry 331, 350, 365, 397, 629, 640, 647, 693
Strainfree growth 723
Striations 34, 39, 268
Surface diffusion 93
Surface energy 3, 84, 183, 186, 225, 236, 380, 790
Surface structure 140, 167, 202, 236, 306, 458
Surface tension 84, 231, 381
Surface thermodynamics 183

Temperature gradient method, *see* Solution growth
Thermal convection 39, 560, 566, 576, 604, 804
Thermodynamics 44, 128, 183, 657, 733, 739, 818
Thin films 27, 48, 131, 135, 159, 167, 174, 202, 217, 225, 302, 306, 315, 319, 325, 331, 336, 342, 346, 360, 371, 397, 410, 571, 651, 777, 814, 818
TV system 619, 624
Twinned structure 829
Two-dimensional phases 164

Unidirectional solidification, *see* Melt growth

Vacancies 252, 257, 276, 640, 693
Vapour deposition 144
Vapour growth 241, 297, 302, 306, 315, 319, 325, 331, 336, 342, 346, 350, 360, 365, 371, 375, 380, 385, 389, 393, 397, 402, 406, 410
Variational formulation 183
Verneuil method, *see* Melt growth

Wetting 231
Whisker growth 9, 62, 191, 198, 346

X-ray topography 34, 252, 257, 262, 268, 272, 285, 342, 427, 814

Zone melting, *see* Melt growth

COMPOUND INDEX

Each page number refers to the first page of a given reference

Ag 191, 217, 225, 417
AgBr 191
AgCl 191
AgI 191
$AgNO_3$ 787
α-Ag_2S 62, 191
α-Ag_2Se 191
α-Ag_2Te 191
Al 252, 777
Al-$CuAl_2$ 739
Al-Mg-Zn 751
Al_2O_3 12, 588
Al_3Ti 777
Alum, ammonium 488
Alum, potassium 500
As 843
ATD-ATG 458
Au 217
Au_2Pb 73
$AuSb_2$ 73
Au-Sn alloy 73

B 97
BN 88
$B_{53}N$ to $B_{28}N$ 350
BP 346
$B_{48}P$ to B_9P 350
$Ba_{0.5}Sr_{0.5}Nb_2O_6$ 555
Be 814
Bi-Au_2Bi 739
Bi-Bi_2Mg_3 739
Bi-Pb alloy 73
Bi-Pb_2Bi 739
Bi-Sn alloy 73
$Bi_{12}TiO_{20}$ 530
Bronze 433

C_6H_{14} 397
Ca 276
$CaCO_3$ 272
CaF_2 276
$CaHPO_4 \cdot 2H_2O$ 476
$CaO \cdot Nb_2O_5$ 675
Cd 123, 198, 810
Cd-CdSb 739
$CdIn_2$ 186
CdS 375
CdSe 375, 657
CdTe 657, 804
CdTe-CdSe 657
CdTe-ZnTe 657
Chalcopyrite 186
CoO 726
Cr_2O_3 588
$CsCoBr_3$ 282
$CsMnBr_3$ 282
Cu 417, 427, 726, 772
Cu-Cu_2Mg 739
Cu-Ni alloys 823
Cuprites 186

Diamond 186

Enargite 186
$Er(OH)_3$ 549

Famatinite 186
$FeBO_3$ 585
α-Fe_2O_3 588
FeSi 406
β-$FeSi_2$ 406
Fe_2Si 406
Fe_5Si_3 406
Fe_2TiO_5 588
Ferrites, ortho- 702
Fluorides 276
Fluorites 186

GaAs 315, 319, 325, 331, 336, 629, 804, 818
$GaAs_{1-x}P_x$ 342
$GaFeO_3$ 588
GaN 360
β-Ga_2O_3 588
GaP 647, 651
Garnets 27, 571, 576, 579
$GdAlO_3$ 560
Ge 315, 726
Ge films, degenerate, 315
GeO_2 524, 604
GeSe 393
$GeSe_2$ 393
GeTe 393
Graphite 97, 164, 186

Halides, complex 282
Hexamethylene tetramine 34
Hg 123
HgS 517
$5Hg(Ch)_2 \cdot 4C_4H_8O$ 207

Ice 9, 236, 241, 483
In 174
InAs 629
InP 640

KBr 217, 441, 726, 787
KCI 217, 454, 726, 787
K.D.P. 462
KI 787
$(KNbO_3)_{10} \cdot (LiNbO_3)_{35} \cdot (BaNb_2O_6)_{55}$ 624
K_2SO_4 510
KVO_3 606

$LiHCl_3$ 397
$LiVO_3$ 686

M_xWO_3 433
Metalorganics 306
$MgAl_2O_4$ 723
Mg-Mg_2Pb 739
Mg-Mg_2Sn 739
Mg_2SiO_4 601
MnSb 747
MnTe 698

NaBr 217
NaCl 217, 787
$NaClO_3$ 493
NaF 217
Na_2O 604
$Na_5P_3O_{10} \cdot 6H_2O$ 449
NaTl 186
$NaVO_3$ 686
Na_2ZnGeO_4 540
Nb_3O 829
Nb_8O 829
Nd-doped crystals 675
NH_4Cl 787
Ni 417
NiAs 186

$Ni_xCo_{1-x}O$ 402
$NiFe_2O_4$ 555, 588
Ni–Nb–Cr 751
NiO 726
$Ni(OH)_2$ 458
$NiTiO_3$ 588
Nitrides 365

PH_3 302
Pb 471, 733
Pb–$AuPb_2$ 739
$PbFe_{12}O_{19}$ 566
PbI_2 787
Pb–Mg_2Pb 739
$Pb(NO_3)_2$ 787
PbSe 657
PbTe 657
PbTe–PbSe 657
Perovskite 186
α-Po 186
Pt 123

Quartz 524

Rare earths 549
– chalcogenides 389
– garnets 27
(R.E.)FeO_3 566
(R.E.)VO_4 588
$RbCoBr_3$ 282
$RbFeBr_3$ 282
$RbFeCl_3$ 282
$RbNiCl_3$ 282
ReO_3 186
Ruby 12, 545

S_4 186
Sapphire 84
(Sb, Bi) 747
Sb–CdSb 739
Sb–InSb 739
(Sb, Sn) 747
Sb–ZnSb 739
ScN 365
Se 843
Si 174, 302
SiC 97, 397
$SiCl_4$ 297
SiH_4 297, 302
Si_2O 604
$Sm_{0.55}Tb_{0.45}FeO_3$ 566
Sn 733
Sn–Mg_2Sn 739
Sphalerite 186
Spherulites 131
$SrTiO_3$ 186
Stannite 186
Steel 782
Succinonitrile 68
Sucrose 483, 787

$TbNbO_4$ 588
ThO_2 588
$ThPbV_2O_8$ 588
TiC 777
TiO_2 78, 202, 524
Ti_2O_3 78
Ti_3O_5 78
Ti_4O_7 to $Ti_{10}O_{19}$ 78
Ti-sillenite 520
Tl 843
Triglycine sulphate 34

Urea 787

VC 693
VN 693
VO 693

W 410
W-bronze 433
WO_3 604
Wurtzite 186, 292

Xe 164

$Y_3Al_5O_{12}$ 286
$YFeO_3$ 706
$Y_3Fe_5O_{12}$ 566
$Y_{20}O_{16}F_{28}$ 566
YVO_4 593
$Yb(OH)_3$ 549

Zn 810
$ZnIn_2S_4$ 385
$Zn_2In_2S_5$ 385
$Zn_3In_2S_6$ 385
ZnS 186, 285, 292
ZnSe 375
ZnTe 657
Zr 535